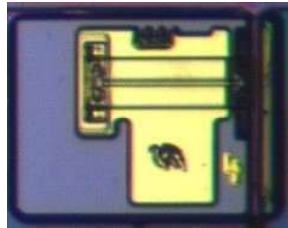


Vertical Emission Laser Chip

VL14000005



Feature

- High power and efficiency
- Cathode bond pad on bottom side.
- Operation temperature -40~85°C

Device Electro-Optical Characteristics

All parameters for T = 25°C unless otherwise noted.

PARAMETER	SYMBOL	UNIT	MIN.	TYP.	MAX.	TEST CONDITIONS
Output power	P	mW		13		I = 50mA
Operating Voltage	V _f	Volt		1.7		I = 50mA
Wavelength	λ	nm	1400		1500	I = 50mA

Device Physical Specifications Single Chip

PARAMETER	UNIT	MIN.	TYP.	MAX.
Bond Pad	um	70*80	75*85	80*90
Chip size	um	185X235	200X250	215X265
Chip Hight	um	105	120	135

Absolute Maximum Ratings

PARAMETER	SYMBOL	UNIT	Ratings
Forward Current	I	mA	80
Reverse Voltage	V _r	Volt	1
Operating Temperature	T _o	°C	-40 to +85
Storage Temperature (Chip on Tape)	T _{st}	°C	5 to +35
Soldering Temperature	T _{so}	°C	260 @10sec

Chip Dimension

